

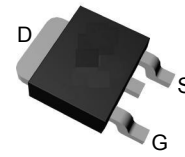
Features

- 40V/100A
 $R_{DS(ON)} = 3.5\text{m}\Omega(\text{typ.}) @ V_{GS} = 10\text{V}$
 $R_{DS(ON)} = 5.5\text{m}\Omega(\text{typ.}) @ V_{GS} = 4.5\text{V}$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)
- Moisture Sensitivity Level MSL1
(per JEDEC J-STD-020D)

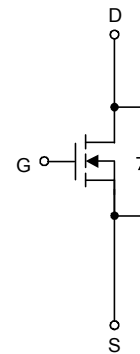
Applications

- Power Management in Desktop Computer or DC/DC Converters

Pin Configuration



Top View of TO-252



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	100	A
I _D	Continuous Drain Current	T _C =25°C	100	A
		T _C =100°C	75	
I _{DM}	Pulse Drain Current	T _C =25°C	300	A
P _D	Maximum Power Dissipation	T _C =25°C	50	W
		T _C =100°C	23.5	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	3.2	°C/W
R _{θJA} ^a	Thermal Resistance-Junction to Ambient	t ≤ 10s	25	°C/W
		Steady State	60	
I _{AS} ^c	Avalanche Current, Single pulse	L=0.1mH	46	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.1mH	106	mJ

Note a : Surface mounted on 1in² pad area, steady state $t = 999\text{s}$.

Note b : Pulse width is limited by max. junction temperature.

Note c : UIS tested and pulse width limited by maximum junction temperature 175 $^{\circ}\text{C}$ (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

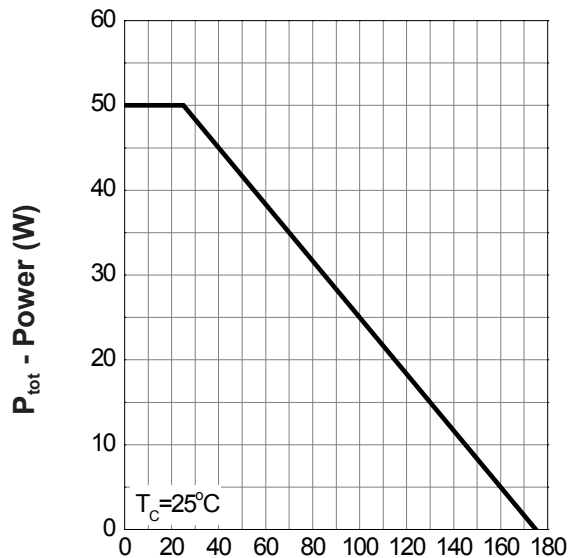
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =32V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.3	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A T _J =125°C V _{GS} =4.5V, I _{DS} =15A	- - -	3.5 6.2 5.5	4.5 - 6.5	mΩ
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =15A	-	21	-	S
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.85	1.1	V
t _{rr}	Reverse Recovery Time	I _{DS} =20A, dI _{SD} /dt=100A/μs	-	18.3	-	ns
t _a	Charge Time		-	8	-	
t _b	Discharge Time		-	10.2	-	
Q _{rr}	Reverse Recovery Charge		-	6.4	-	nC
Dynamic Characteristics [°]						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, Frequency=1.0MHz	-	4204	4871	pF
C _{oss}	Output Capacitance		-	336	-	
C _{rss}	Reverse Transfer Capacitance		-	251	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, R _L =20Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	11.3	21	ns
t _r	Turn-on Rise Time		-	8.2	15	
t _{d(OFF)}	Turn-off Delay Time		-	22.6	41	
t _f	Turn-off Fall Time		-	15.4	28	
Gate Charge Characteristics [°]						
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _{DS} =20A	-	15	21	nC
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =4.5V, I _{DS} =20A	-	7.1	-	
Q _{gth}	Threshold Gate Charge		-	1.65	-	
Q _{gs}	Gate-Source Charge		-	3.2	-	
Q _{gd}	Gate-Drain Charge		-	1.9	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

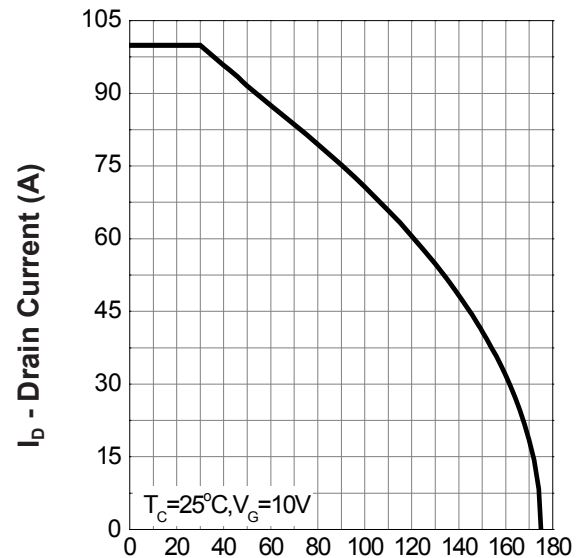
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

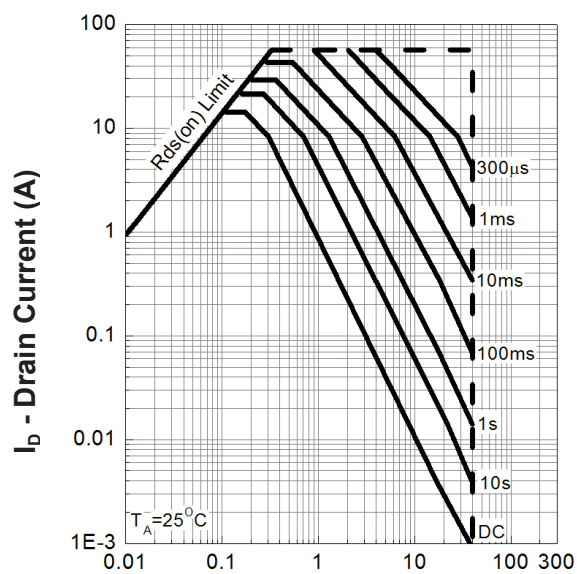
Power Dissipation



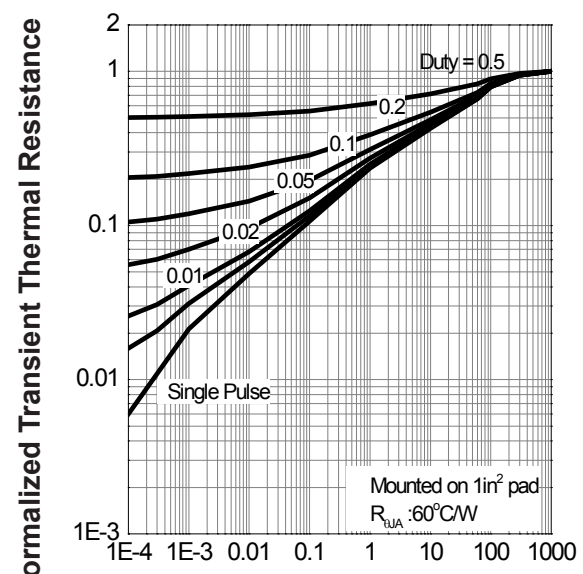
Drain Current



Safe Operation Area

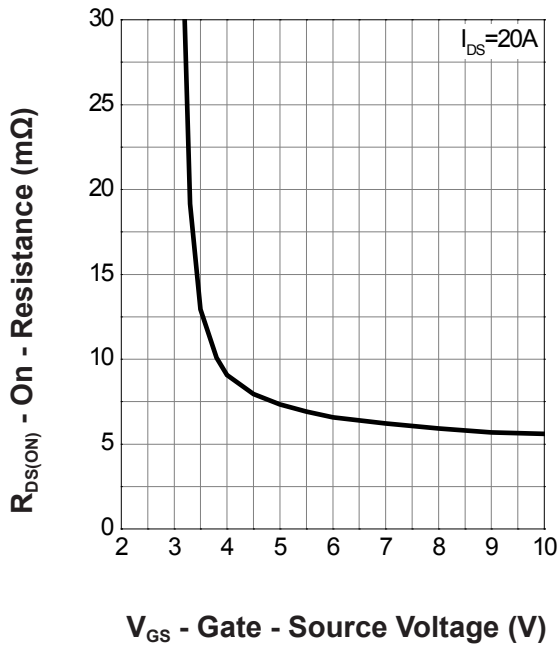


Thermal Transient Impedance

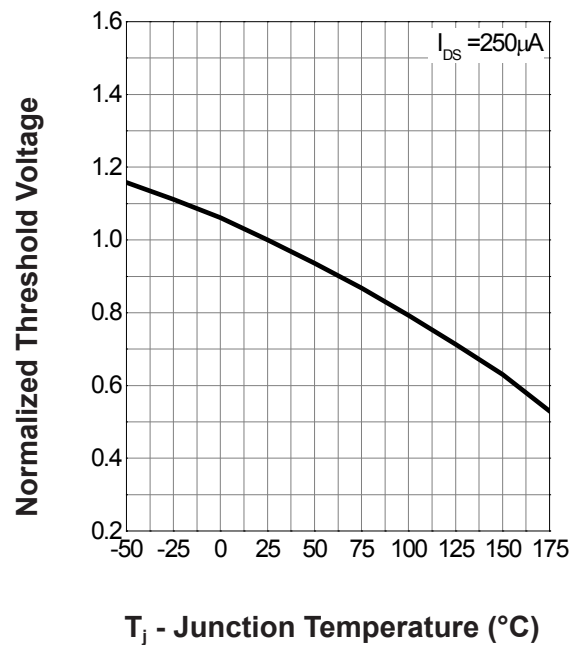


Typical Operating Characteristics(Cont.)

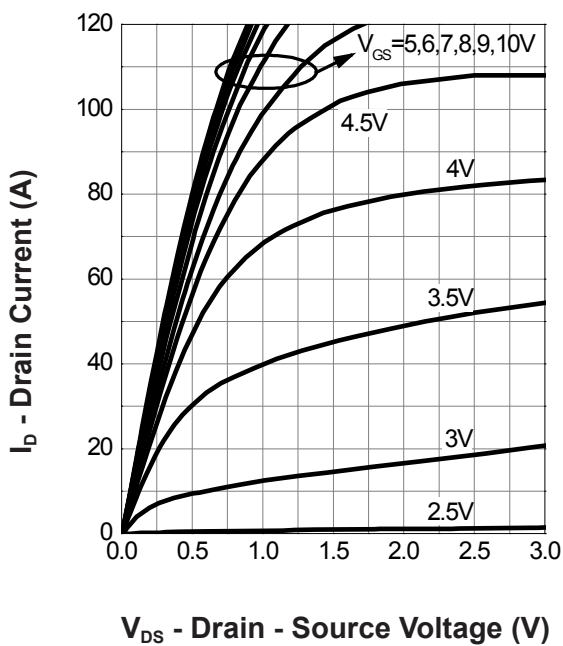
Gate-Source On Resistance



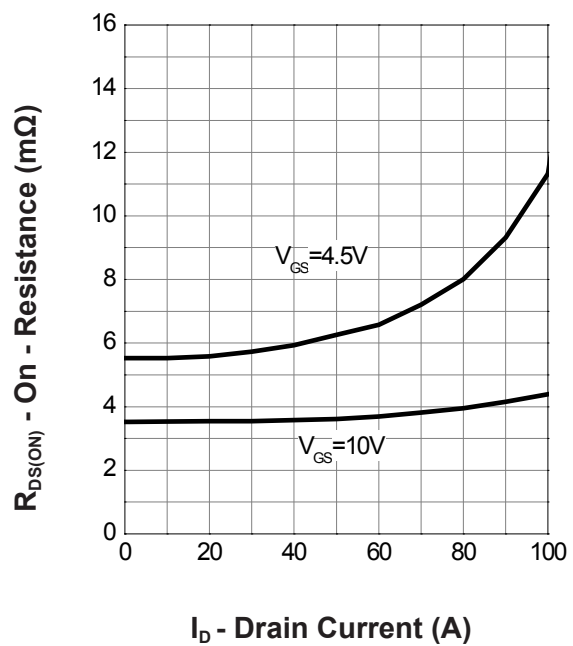
Gate Threshold Voltage



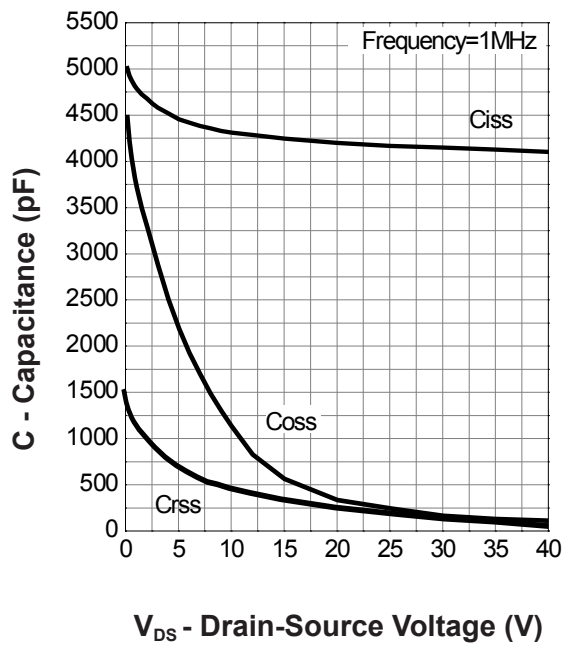
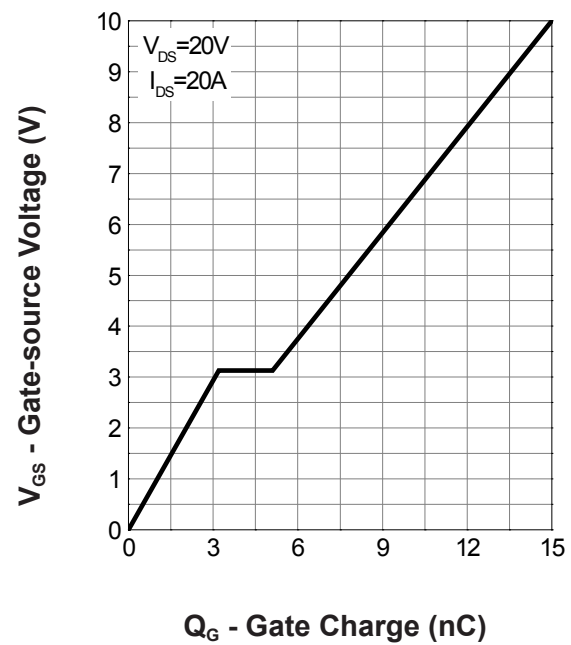
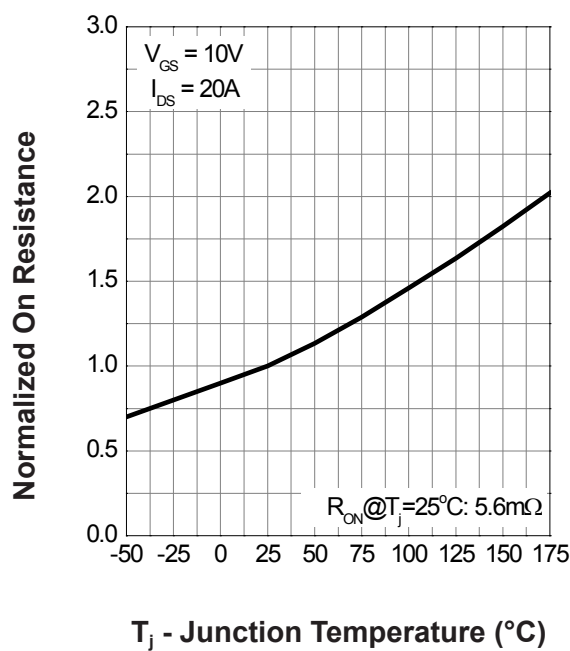
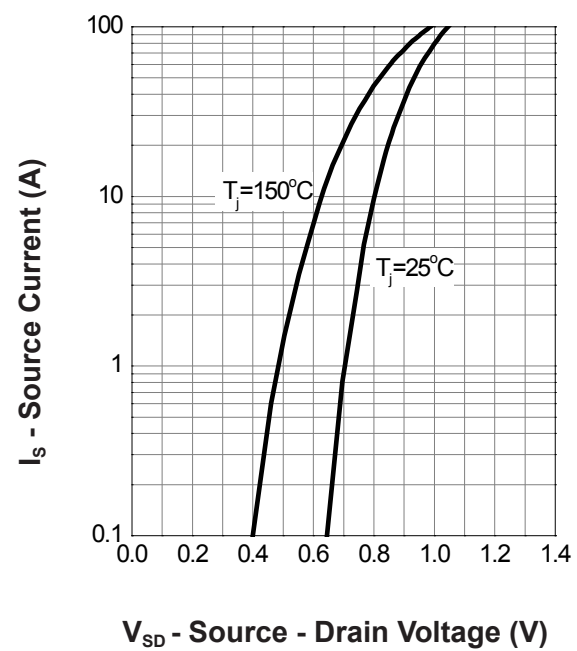
Output Characteristics



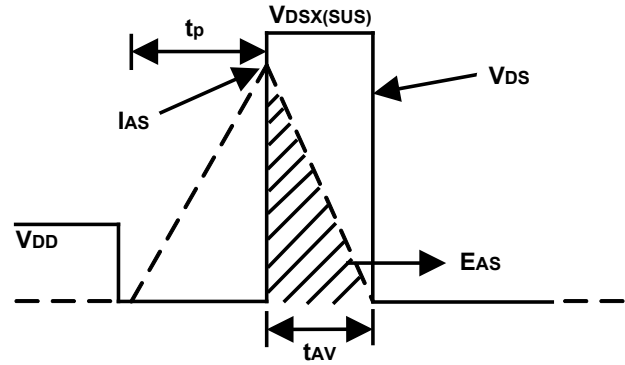
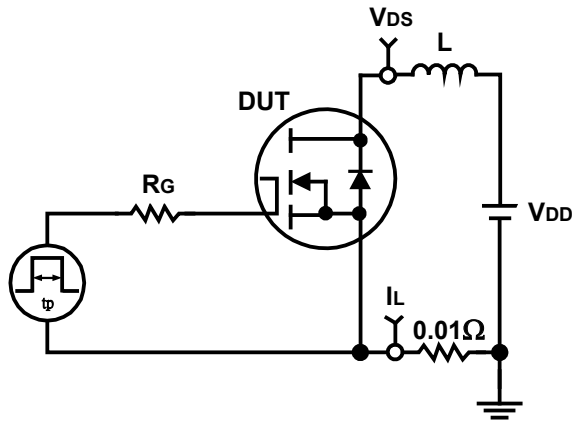
Drain-Source On Resistance



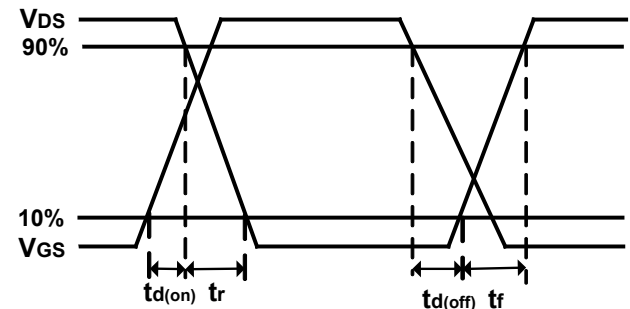
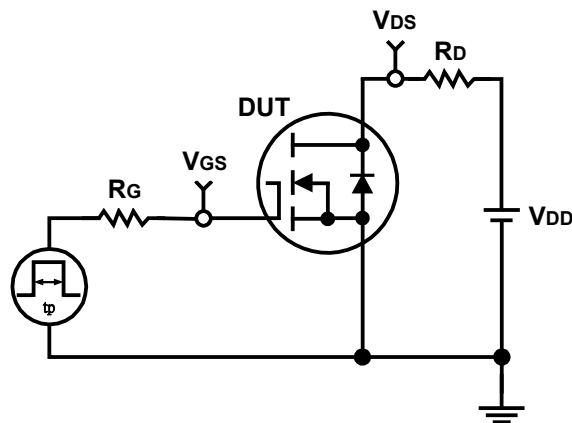
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

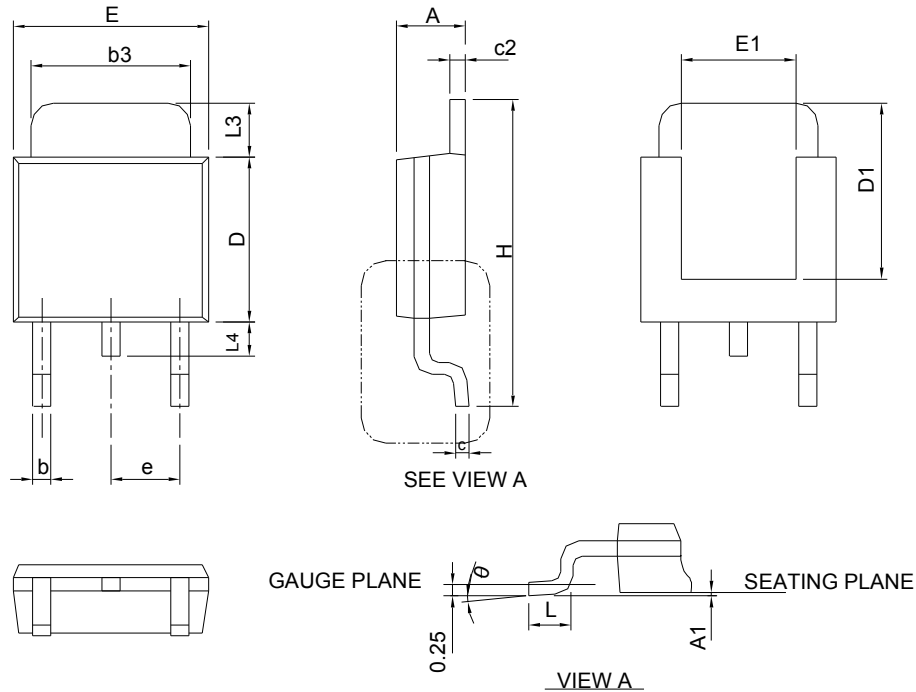


Switching Time Test Circuit and Waveforms



Package Information

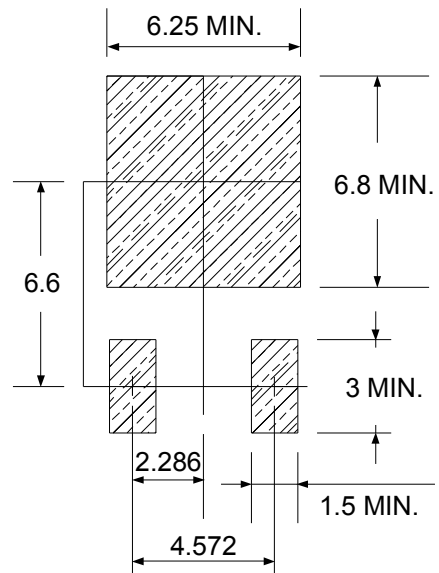
TO-252



SYMBOL	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252 .

RECOMMENDED LAND PATTERN



UNIT: mm